

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Not for submission under 37 CFR 1.99)	Application Number	10/586,543
	Confirmation Number	6159
	Filing Date	July 19, 2006
	First Named Inventor	Yasuhito URASHIMA
	Art Unit	2826
	Examiner Name	AHMED, SELIM U
	Attorney Docket Number	Q79654

U.S. PATENTS						
Examiner Initials*	Cite No	Patent Number	Kind Code <sup>1</sup>	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

U.S. PATENT APPLICATION PUBLICATIONS						
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FOREIGN PATENT DOCUMENTS								
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NON-PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	T <sup>5</sup>
	1.	Takahiro ITO, et al.; "Influence of Thermal Annealing on GaN Buffer Layers and the Property of Subsequent GaN Layers Grown by Metalorganic Chemical Vapor Deposition"; Jpn. J. Appl. Phys., Part 1, Vol. 38, No. 2A; February 1999; pp. 649-653; XP-002616994	
	2.	Shigekazu SANO, et al.; "Low-dislocation-density GaN and $\text{G}_{1-x}\text{Al}_x\text{N}$ ( $x \leq 0.13$ ) grown on grooved substrates; Journal of Crystal Growth; Vol. 234, No. 1-4; 1 February 2002; pp. 129-134; XP 004333449	
	3.	A. Kakanakova-Georgieva, et al.; "Epitaxial Growth of AlN Layers on SiC Substrates in a Hot-Wall MOCVD System"; phys. stat. sol. (c) Vol. 0; No. 1; 2002; pp. 205-208; XP-002616996	
	4.	J.A. POWELL, et al.; "Process-Induced Morphological Defects in Epitaxial CVD Silicon Carbide"; phys. stat. sol. (b); Vol. 202, No. 1; 1 July 1997; pp. 529-548; XP-002616995	

EXAMINER SIGNATURE			
Examiner Signature		Date Considered	

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## **CERTIFICATION STATEMENT**

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

- ☒ That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(1).

**OR**

- ☐ That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).

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- ☒ Fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

- ☒ The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

- ☐ None

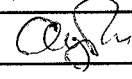
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## **SIGNATURE**

A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature		Date (YYYY-MM-DD)	2011-02-28
Name/Print	Abraham J. Rosner	Registration Number	33,276

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